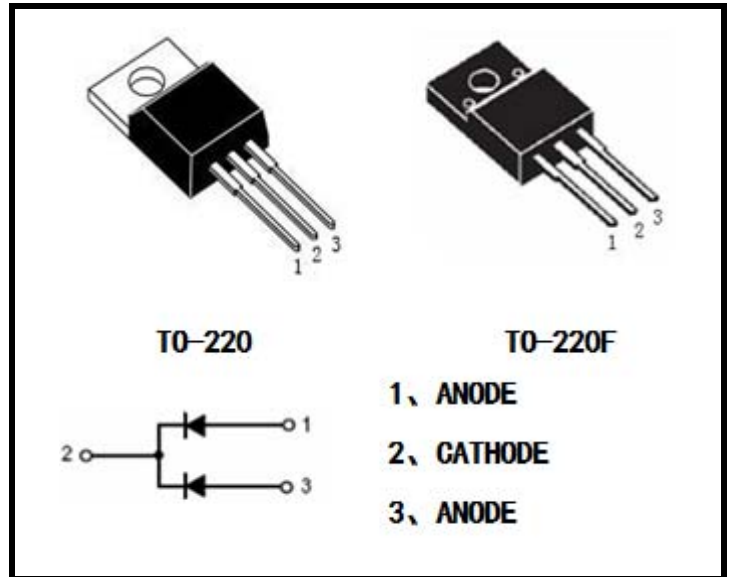


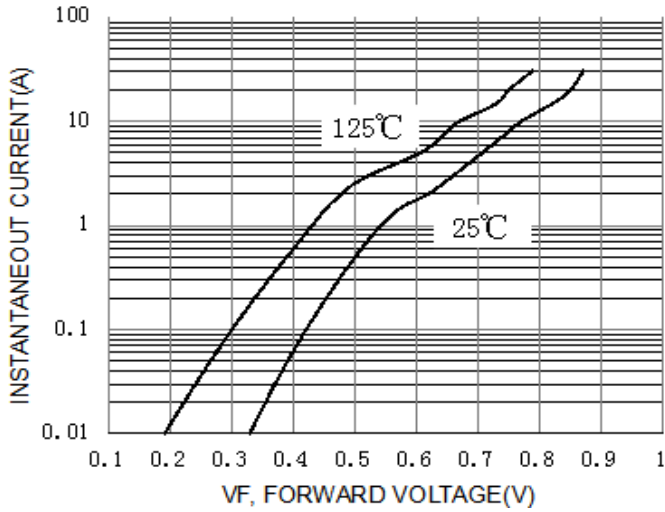
Ultra Low $V_F=0.52V$ at $I_F=2A$
FEATURES

- * Schottky Barrier Chip
- * Guard Ring Die Construction for Transient Protection
- * Low Power Loss, High Efficiency
- * High Surge Capability
- * High Current Capability and Low Forward Voltage Drop
- * For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

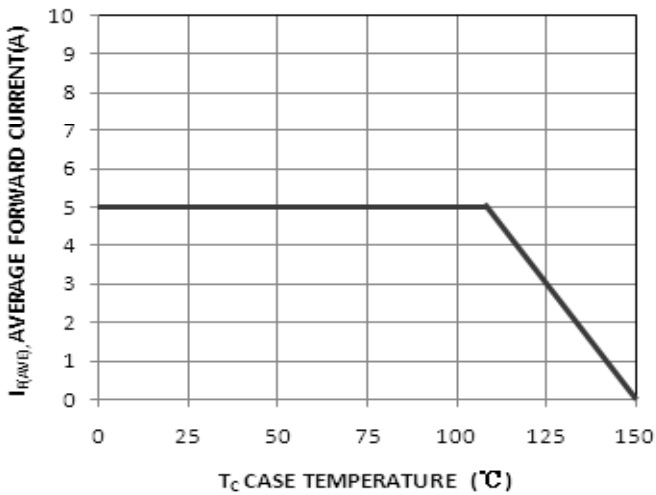
PACKAGE

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$)

Characteristic	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage	V_{RRM}	150	V	
Working Peak Reverse Voltage	V_{RWM}			
DC Blocking Voltage	V_R			
Average Rectified Output Current	$I_{F(per\ leg)}$	5	A	
	$I_{F(Total)}$	10		
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60Hz)	I_{FSM}	200	A	
Instantaneous Forward Voltage @ $I_F=2A, T_C=25^{\circ}C$ @ $I_F=5A, T_C=25^{\circ}C$ @ $I_F=2A, T_C=125^{\circ}C$ @ $I_F=5A, T_C=125^{\circ}C$	V_F	TYP.	V	
		0.64		
		0.73		
		0.52		
Peak Reverse Current @ $T_c=25^{\circ}C$ at Rated DC Blocking Voltage @ $T_c=125^{\circ}C$	I_R	0.1	mA	
		20		
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	$^{\circ}C$	
Maximum Thermal Resistance	θ_{JC}	TO-220	2	$^{\circ}C/W$
		TO-220F	4	
	θ_{JA}	TO-220	60	
		TO-220F	60	

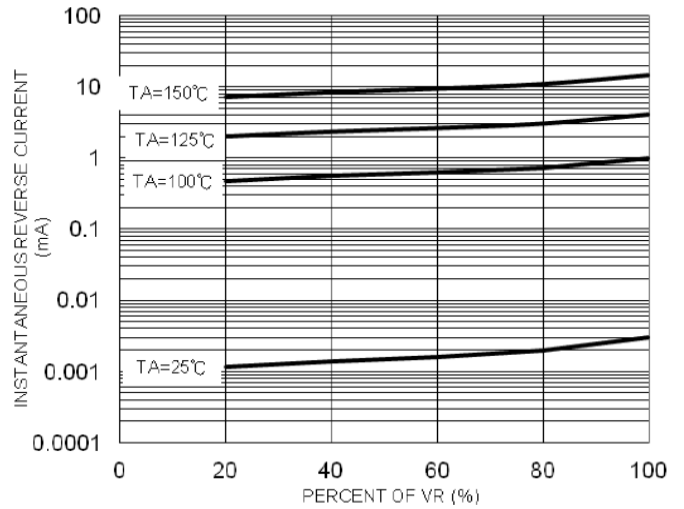
■ Characteristics Curves



Typical Forward Voltage Per Diode

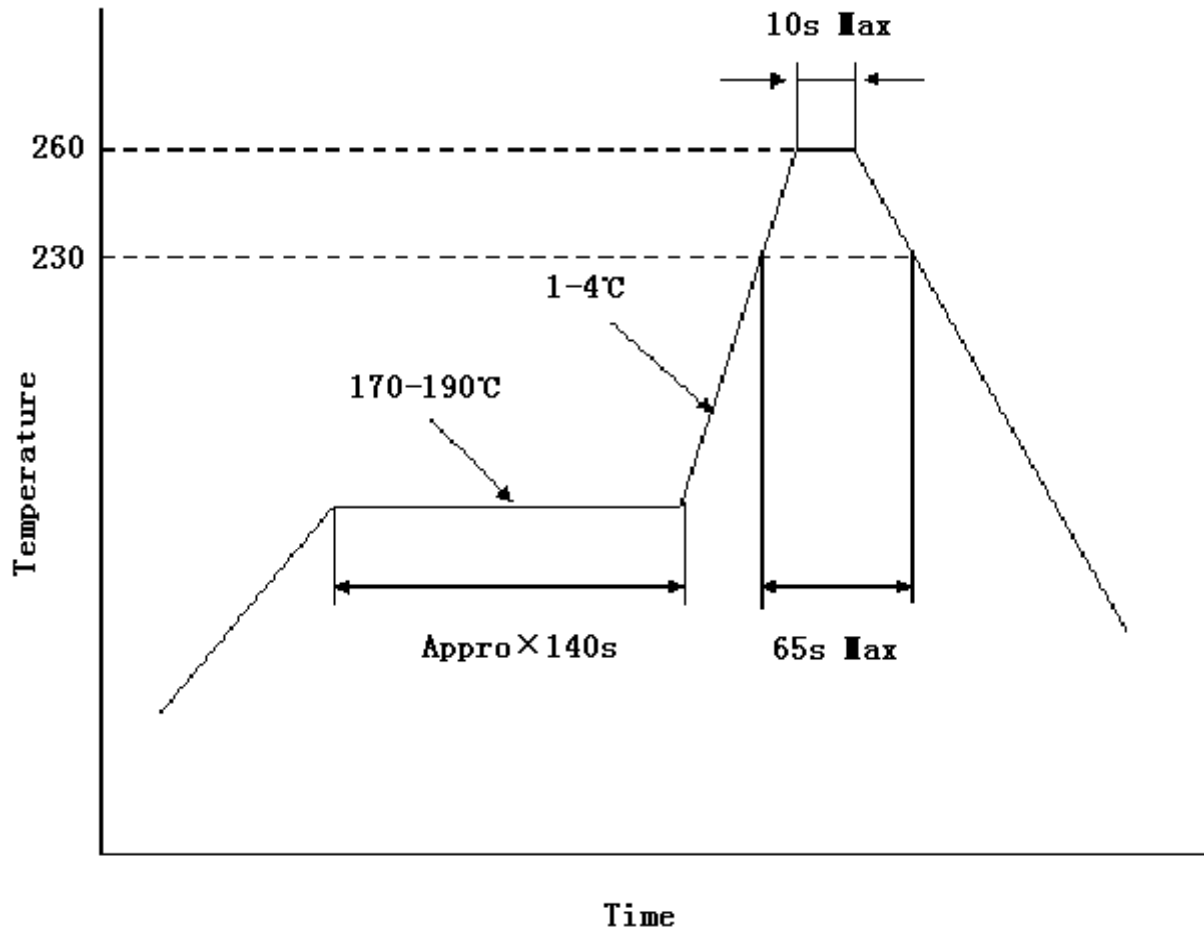


Average Forward Current vs. Case Temperature Per Diode



Typical Reverse Current Per Diode

■ Reflow Soldering Temperature Profile



T0-220 MECHANICAL DATA

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4		4.8	e	2.44	2.54	2.64
B	1.2		1.4	F	1.1		1.4
B1	1		1.4	L	12.5		14.5
b1	0.75		0.95	L1	3	3.5	4
c	0.4		0.55	ΦP	3.7	3.8	3.9
D	15		16.5	Q	2.5		3
D1	5.9		6.9	Q1	2		2.9
E	9.9		10.7				

